DUAL P-CHANNEL MOSFET

–20 V, –3.0 A, 79 mΩ

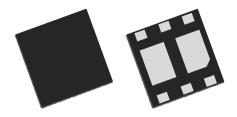
Description

The μ PA2670T1R is Dual P-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- -1.8V drive available
- Low on-state resistance
 - ---- $R_{DS (on)1} = 79 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -4.5 \text{ V}$, $I_D = -1.5 \text{ A}$)
 - ---- $R_{DS (on)2} = 105 \text{ m}\Omega \text{ MAX}. (V_{GS} = -2.5 \text{ V}, I_D = -1.5 \text{ A})$
 - ---- $R_{DS (on)3} = 182 \text{ m}\Omega \text{ MAX}. (V_{GS} = -1.8 \text{ V}, I_D = -1.5 \text{ A})$
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020(Dual)

Ordering Information

Part Number	Package		
μPA2670T1R-E2-AX* ¹	6pinHUSON2020		

Note: *1.Pb-free (This product does not contain Pb in the external electrode and other parts.)

Absolute Maximum Ratings (T_A = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 V$)	V _{DSS}	-20	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	∓10	V
Drain Current (DC)	I _{D(DC)}	∓3.0	А
Drain Current (pulse) *1	I _{D(pulse)}	∓12	А
Total Power Dissipation (1 unit, 5 s) *2	P _{T1}	1.5	W
Total Power Dissipation (2 units, 5 s) *2	P _{T2}	2.3	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{STG}	–55 to +150	°C

Notes: ∗1. PW≤10 µs, Duty Cycle≤1%

*2. Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt

Data Sheet



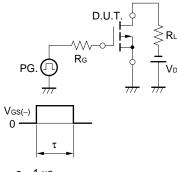
Electrical Characteristics (T_A = 25°C)

Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions	
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μA	V_{DS} = -20 V, V_{GS} = 0 V	
Gate Leakage Current	I _{GSS}			∓10	μA	V _{GS} = ∓8 V, V _{DS} = 0 V	
Gate Cut-off Voltage	V _{GS(off)}	-0.4		-1.1	V	V_{DS} = -10 V, I_{D} = -1 mA	
Forward Transfer Admittance *1	y _{fs}	4.5			S	V_{DS} = -5 V, I _D = -2 A	
Drain to Source On-state	R _{DS(on)1}		63	79	mΩ	V_{GS} = -4.5 V, I _D = -1.5 A	
Resistance *1	R _{DS(on)2}		78	105	mΩ	V_{GS} = -2.5 V, I _D = -1.5 A	
	R _{DS(on)3}		109	182	mΩ	V_{GS} = -1.8 V, I _D = -1.5 A	
Input Capacitance	C _{iss}		473		pF	V_{DS} = -10 V, V_{GS} = 0 V,	
Output Capacitance	C _{oss}		88		pF	f = 1.0 MHz	
Reverse Transfer Capacitance	C _{rss}		68		pF		
Turn-on Delay Time	t _{d (on)}		11.5		ns	$I_D = -1.5 \text{ A}, V_{DD} = -10.0 \text{ V},$ $V_{GS} = -4.0 \text{ V}, \text{ R}_G = 6 \Omega$	
Rise Time	tr		4.0		ns		
Turn-off Delay Time	t _{d (off)}		37.5		ns		
Fall Time	t _f		12.5		ns		
Total Gate Charge	Q _G		5.1		nC	$I_D = -3.0 \text{ A}$, $V_{DD} = -16 \text{ V}$,	
Gate to Source Charge	Q _{GS}		0.9		nC	V _{GS} = -4.5 V	
Gate to Drain Charge	Q _{GD}		1.5		nC]	
Body Diode Forward Voltage *1	V _{F(S-D)}			1.5	V	I _F = 3.0 A, V _{GS} = 0 V	

Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME

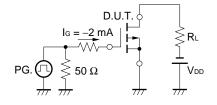
Vdd



 $\tau = 1 \, \mu s$, Duty Cycle ≤ 1%

Vgs(-) VGS Wave Form 90% 0 10% Vgs Vds(-) 90% 90% Vds V_{DS} Wave Form 10% 10% 0 tf tr td(on) td(off) tor toff

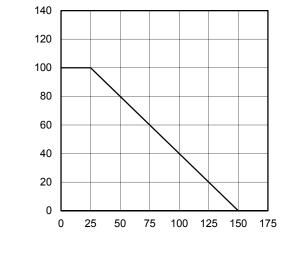
TEST CIRCUIT 2 GATE CHARGE





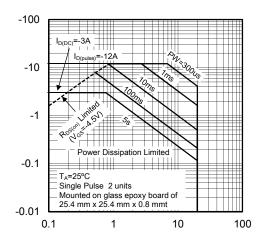
Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

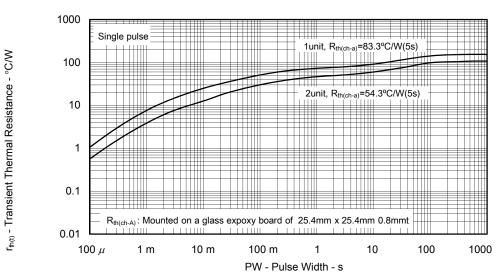


 T_A -Ambient Temperature - $^\circ C$

FORWARD BIAS SAFE OPERATING AREA

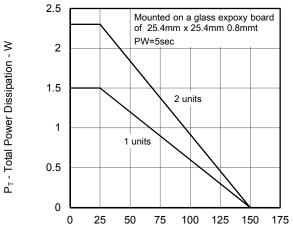


V_{DS} - Drain to Source Voltage - V



TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

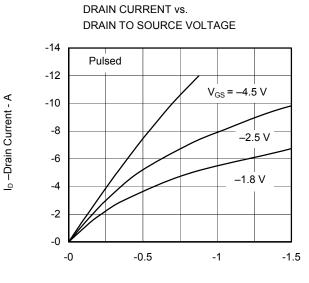
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



T_A -Ambient Temperature - °C

dT - Percentage of Rated Power - %

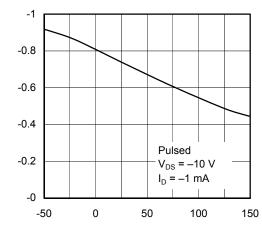






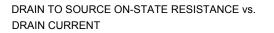


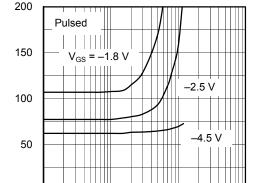






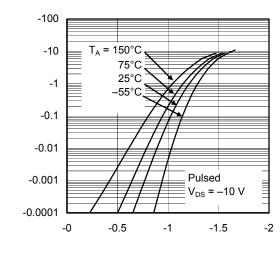








FORWARD TRANSFER CHARACTERISTICS



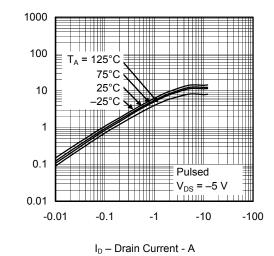
I_D - Drain Current - A

| y_{fs} | - Forward Transfer Admittance - S

 $R_{DS(on)}$ – Drain to Source On-state Resistance - m Ω

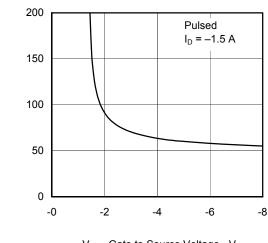
 V_{GS} - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs.

GATE TO SOURCE VOLTAGE



 V_{GS} - Gate to Source Voltage - V

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-0.1



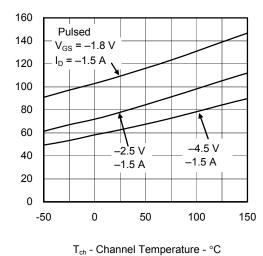
-100

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

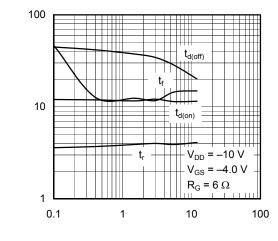


t_{d(on)}, t_f, t_{d(off)}, t_r - Switching Time - μ s

I_F - Diode Forward Current – A

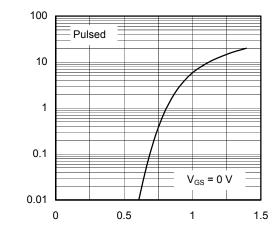


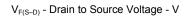




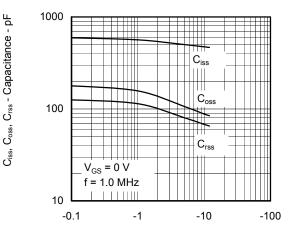
I_D - Drain Current - A

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



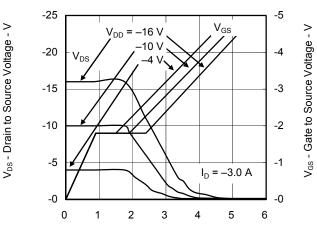


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



V_{DS} – Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

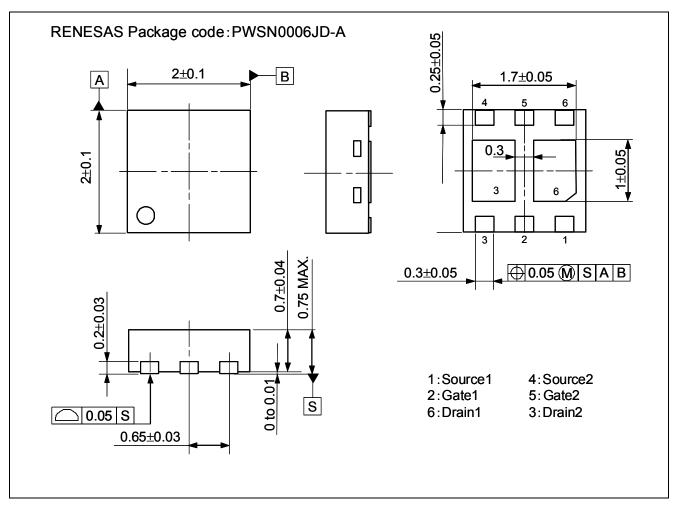


Q_G - Gate Charge - nC

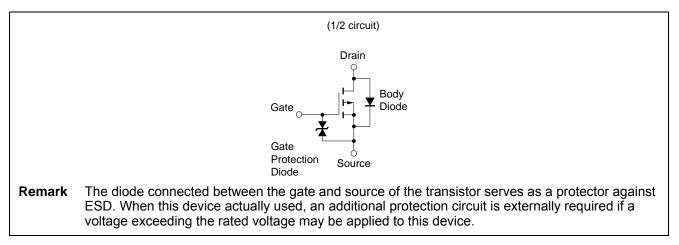


Package Drawings (Unit: mm)

6pinHUSON2020



Equivalent Circuit





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